NGTD13T65F2

IGBT Die

Trench Field Stop II IGBT Die for motor drive and inverter applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Low V_{CE(sat)} Loss Reduces System Power Dissipation

Typical Applications

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, T _J = 25°C	V_{CE}	650	V
DC Collector Current, limited by T _{J(max)}	I _C	(Note 1)	Α
Pulsed Collector Current (Note 2)	I _{C, pulse}	120	Α
Gate-Emitter Voltage	V_{GE}	±20	V
Maximum Junction Temperature	T_J	-55 to +175	°C
Short Circuit Withstand Time, $V_{GE} = 15 \text{ V}, V_{CE} = 400 \text{ V}, T_J \le 150^{\circ}\text{C}$	T _{SC}	5.0	μS

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Depending on thermal properties of assembly. 2. T_{pulse} limited by T_{jmax} , 5.0 μs pulse, V_{GE} = 15 V.

MECHANICAL DATA

Parameter	Value	Unit	
Die Size	3550 x 3550	μm ²	
Emitter Pad Size	See die layout	μm ²	
Gate Pad Size	410 x 670	μm ²	
Die Thickness	3	mils	
Wafer Size	150	mm	
Top Metal	4 μm AISI		
Back Metal	2 μm TiNiAg		
Max possible chips per wafer	996		
Passivation frontside	Oxide-Nitride		
Reject ink dot size	25 mils		
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH		pe in ring-pack e: < 3 months	

ORDERING INFORMATION

Device	Inking?	Shipping
NGTD13T65F2WP	Yes	Bare Wafer on Tape
NGTD13T65F2SWK	Yes	Sawn Wafer on Tape

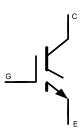


ON Semiconductor®

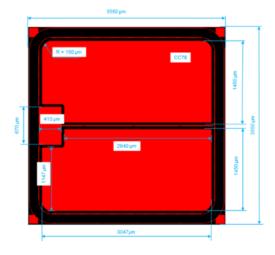
www.onsemi.com

 $V_{RCE} = 650 V$ I_C = Limited by $T_{J(max)}$

IGBT DIE



DIE OUTLINE



NGTD13T65F2

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

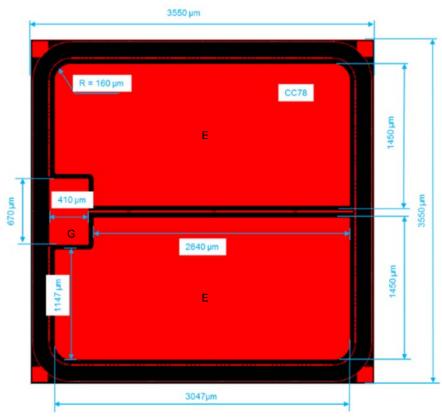
						1
Parameter	Test Conditions	Symbol	Min	Тур	Max	Units
STATIC CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 500 \mu A$	V _{(BR)CES}	650			V
Collector-Emitter Saturation Voltage	V _{GE} = 15 V, I _C = 30 A	V _{CE(sat)}		1.6	2.2	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_{C} = 350 \mu A$	V _{GE(TH)}	4.5	5.5	6.5	V
Collector-Emitter Cutoff Current	V _{GE} = 0 V, V _{CE} = 650 V	I _{CES}			0.2	mA
Gate Leakage Current	V _{GE} = 20 V, V _{CE} = 0 V	I _{GES}			100	nA

DYNAMIC CHARACTERISTICS

Input Capacitance		C _{ies}	3200	pF
Output Capacitance	$V_{CE} = 20 \text{ V}, V_{GE} = 0 \text{ V}, f = 1$ MHz	C _{oes}	130	pF
Reverse Transfer Capacitance		C _{res}	85	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



E = Emitter pad G = Gate pad All dimensions in μm

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales